

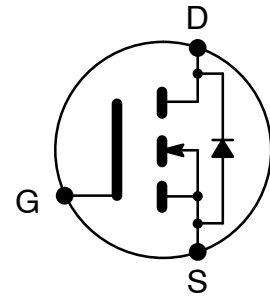


ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE2900 MOSFET N-Ch, Enhancement Mode High Speed Switch TO220 Type Package

Features:

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements



Absolute Maximum Ratings:

Continuous Drain Current ($V_{GS} = 10V$), I_D	
$T_C = +25^\circ C$	14A
$T_C = +100^\circ C$	8.5A
Pulsed Drain Current (Note 1), I_{DM}	56A
Power Dissipation ($T_C = +25^\circ C$), P_D	125W
Derate Linearly Above $25^\circ C$	1.0W/ $^\circ C$
Gate-to-Source Voltage, V_{GS}	± 20
Single Pulse Avalanche Energy (Note 2), E_{AS}	550mJ
Avalanche Current (Note 1), I_{AR}	14A
Repetitive Avalanche Energy (Note 1), E_{AR}	13mJ
Peak Diode Recovery dv/dt (Note 3), dv/dt	4.8V/ns
Operating Junction Temperature Range, T_J	-55° to $+175^\circ C$
Storage Temperature Range, T_{stg}	-55° to $+175^\circ C$
Lead Temperature (During Soldering, 1.6mm from case for 10sec), T_L	$+300^\circ C$
Mounting Torque (6-32 or M3 Screw)	10 lbf•in (1.1N•m)
Thermal Resistance, Junction-to-Case, R_{thJC}	$1.0^\circ C/W$
Thermal Resistance, Junction-to-Ambient, R_{thJA}	$62^\circ C/W$
Typical Thermal Resistance, Case-to-Sink (Flat, Greased Surface), R_{thCS}	$0.5^\circ C/W$

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 2. $V_{DD} = 25V$, starting $T_J = +25^\circ C$, $L = 4.5mH$, $R_G = 25\pm$, $I_{AS} = 14A$

Note 3. $I_{SD} \leq 14A$, di/dt $\leq 150A/\mu s$, $V_{DD} \leq 250V$, $T_J \leq +175^\circ C$

Note 4. Pules Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\leq A$	250	-	-	V
Breakdown Voltage Temp. Coefficient	$\frac{V_{(BR)DSS}}{T_J}$	Reference to $+25^\circ\text{C}$, $I_D = 1\text{mA}$	-	0.34	-	$V/^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 8.4A$, Note 4	-	-	0.28	\pm
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\leq A$	2.0	-	4.0	V
Forward Transconductance	g_{fs}	$V_{DS} = 50V, I_D = 8.4A$, Note 4	6.7	-	-	mhos
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = 250V, V_{GS} = 0V$	-	-	25	$\leq A$
		$V_{DS} = 200V, V_{GS} = 0V, T_J = +125^\circ\text{C}$	-	-	250	$\leq A$
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = 20V$	-	-	100	nA
Gate-to-Source Reverse Leakage	I_{GSS}	$V_{GS} = -20V$	-	-	-100	nA
Total Gate Charge	Q_g	$I_D = 7.9A, V_{DS} = 200V, V_{GS} = 10V$, Note 4	-	-	68	nC
Gate-to-Source Charge	Q_{gs}		-	-	11	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	-	35	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 125V, I_D = 7.9A, R_G = 9.1\pm$, $R_D = 8.7\pm$, Note 4	-	11	-	ns
Rise Time	t_r		-	24	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	53	-	ns
Fall Time	t_f		-	49	-	ns
Internal Drain Inductance	L_D	Between lead, .250in. (6.0) mm from package and center of die contact	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	nH
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$	-	1300	-	pF
Output Capacitance	C_{oss}		-	330	-	pF
Reverse Transfer Capacitance	C_{riss}		-	85	-	pF

Source-Drain Ratings and Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Source Current (Body Diode)	I_S		-	-	14	A
Pulsed Source Current (Body Diode)	I_{SM}	Note 1	-	-	56	A
Diode Forward Voltage	V_{SD}	$T_J = +25^\circ\text{C}, I_S = 14A, V_{GS} = 0V$, Note 4	-	-	1.8	V
Reverse Recovery Time	t_{rr}	$T_J = +25^\circ\text{C}, I_F = 7.9A$, $di/dt = 100A/\leq s$, Note 4	-	250	500	ns
Reverse Recovery Charge	Q_{rr}		-	2.3	4.6	$\leq C$
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Note 1. Repetitive rating; pulse width limited by maximum junction temperature.

Note 4. Pulse width $\leq 300\leq s$; duty cycle $\leq 2\%$.



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [NTE](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#) [424134F](#)
[026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#) [IPS70R2K0CEAKMA1](#)
[RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#) [NTE6400](#) [JANTX2N6796U](#)
[JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#) [2SK2614\(TE16L1,Q\)](#)